



NEC's NPN SILICON TRANSISTOR NE685M13

FEATURES

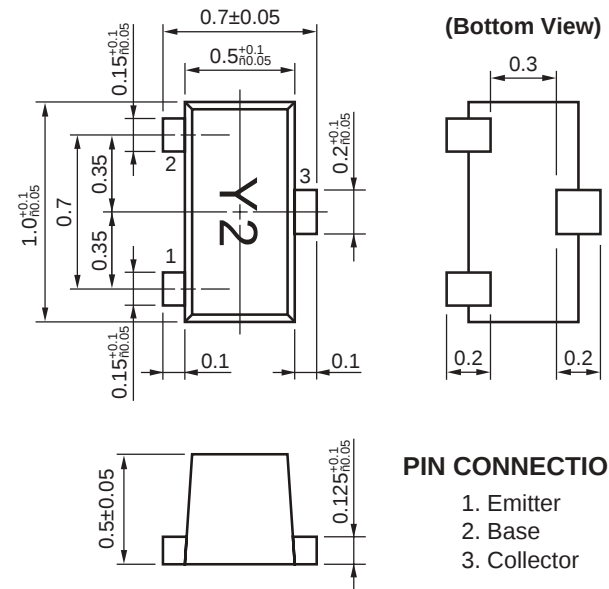
- **NEW MINIATURE M13 PACKAGE:**
 - Small transistor outline
 - 1.0 X 0.5 X 0.5 mm
 - Low profile / 0.50 mm package height
 - Flat lead style for better RF performance
- **HIGH GAIN BANDWIDTH PRODUCT:**
 $f_T = 12 \text{ GHz}$
- **LOW NOISE FIGURE:**
 $NF = 1.5 \text{ dB at } 2 \text{ GHz}$

DESCRIPTION

NEC's NE685M13 transistor is designed for low noise, high gain, and low cost requirements. This high f_T part is well suited for low voltage/low current designs for portable wireless communications and cellular radio applications. NEC's new low profile/flat lead style "M13" package is ideal for today's portable wireless applications. The NE685 is also available in six different low cost plastic surface mount package styles.

OUTLINE DIMENSIONS (Units in mm)

PACKAGE OUTLINE M13



ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)

PART NUMBER EIAJ ¹ REGISTERED NUMBER PACKAGE OUTLINE		NE685M13 2SC5617 M13			
SYMBOLS	PARAMETERS AND CONDITIONS	UNITS	MIN	TYP	MAX
f_T	Gain Bandwidth at $V_{CE} = 3 \text{ V}$, $I_C = 10 \text{ mA}$, $f = 2 \text{ GHz}$	GHz		12.0	
NF	Noise Figure at $V_{CE} = 3 \text{ V}$, $I_C = 3 \text{ mA}$, $f = 2 \text{ GHz}$, $Z_S = Z_{OPT}$	dB		1.5	2.5
$ S_{21E} ^2$	Insertion Power Gain at $V_{CE} = 3 \text{ V}$, $I_C = 10 \text{ mA}$, $f = 2 \text{ GHz}$	dB	7.0	11.0	
h_{FE}^2	Forward Current Gain at $V_{CE} = 3 \text{ V}$, $I_C = 10 \text{ mA}$		75		140
I_{CBO}	Collector Cutoff Current at $V_{CB} = 5 \text{ V}$, $I_E = 0$	μA			0.1
I_{EBO}	Emitter Cutoff Current at $V_{EB} = 1 \text{ V}$, $I_C = 0$	μA			0.1
C_{RE}^3	Feedback Capacitance at $V_{CB} = 3 \text{ V}$, $I_E = 0$, $f = 1 \text{ MHz}$	pF		0.4	0.7

Notes:

1. Electronic Industrial Association of Japan.
2. Pulsed measurement, pulse width $\leq 350 \mu\text{s}$, duty cycle $\leq 2 \%$.
3. Capacitance is measured with emitter and case connected to the guard terminal at the bridge.

ABSOLUTE MAXIMUM RATINGS¹ (T_A = 25°C)

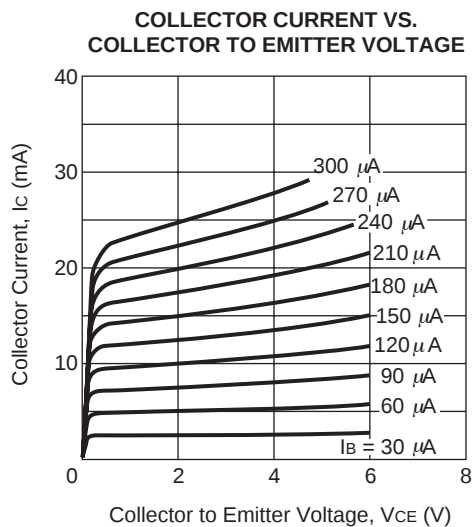
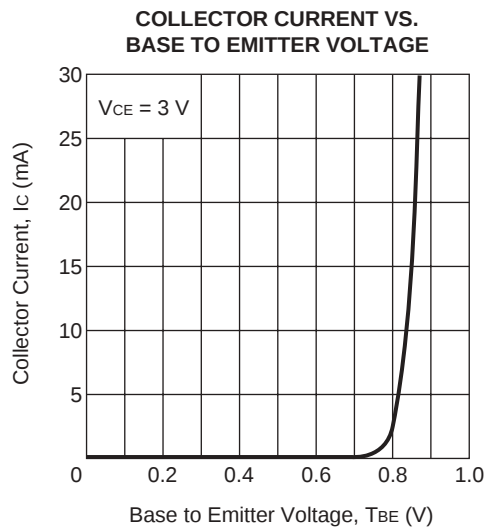
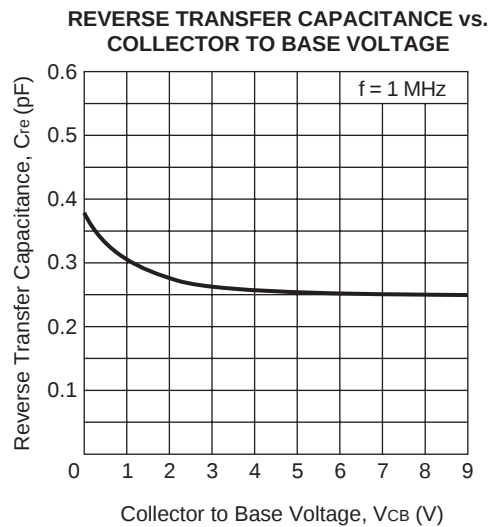
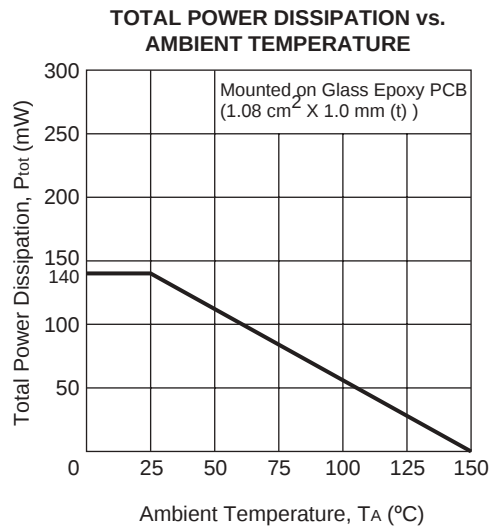
SYMBOLS	PARAMETERS	UNITS	RATINGS
V _{CB0}	Collector to Base Voltage	V	9.0
V _{CEO}	Collector to Emitter Voltage	V	6.0
V _{EB0}	Emitter to Base Voltage	V	2.0
I _C	Collector Current	mA	30
P _T ²	Total Power Dissipation	mW	140
T _J	Junction Temperature	°C	150
T _{STG}	Storage Temperature	°C	-65 to +150

- Notes:
1. Operation in excess of any one of these parameters may result in permanent damage.
 2. With device mounted on 1.08 cm² X 1.2 mm thick glass epoxy PCB.

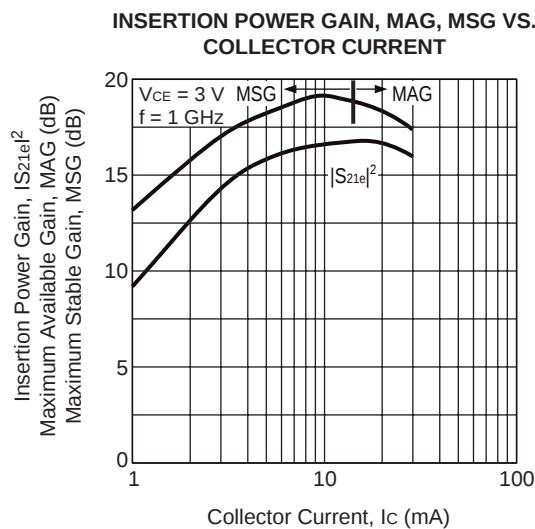
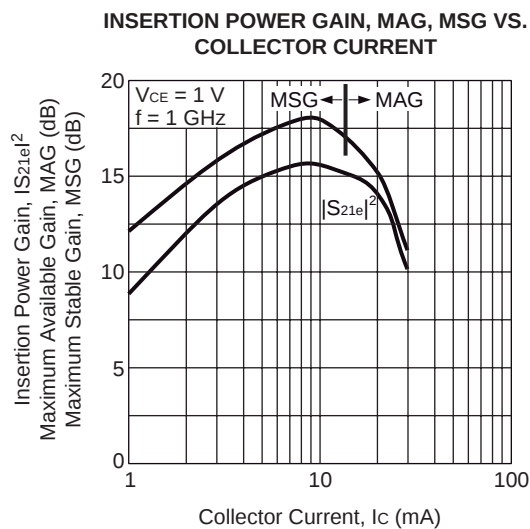
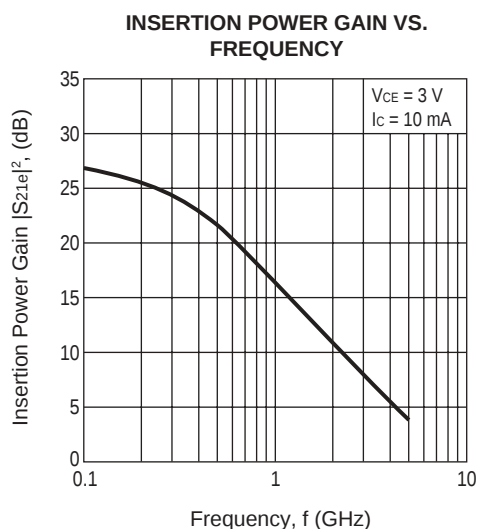
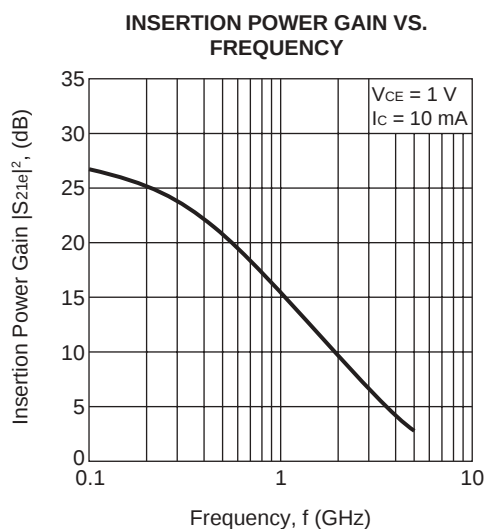
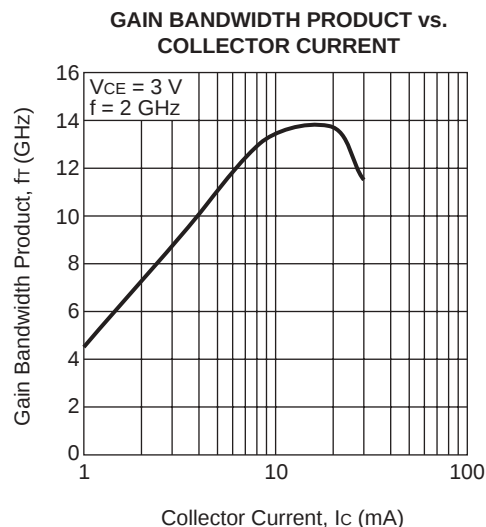
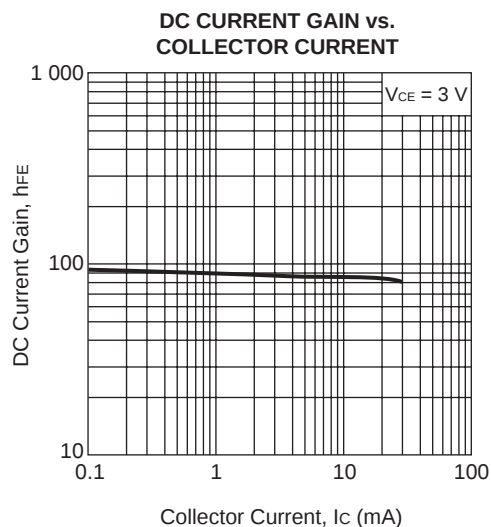
ORDERING INFORMATION

PART NUMBER	QUANTITY
NE685M13-T3	3k pcs./reel

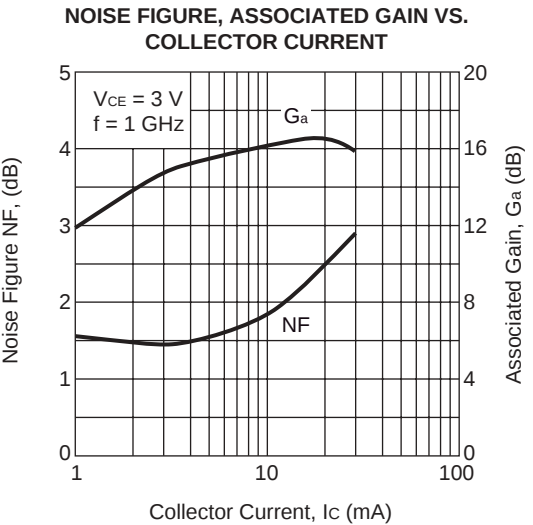
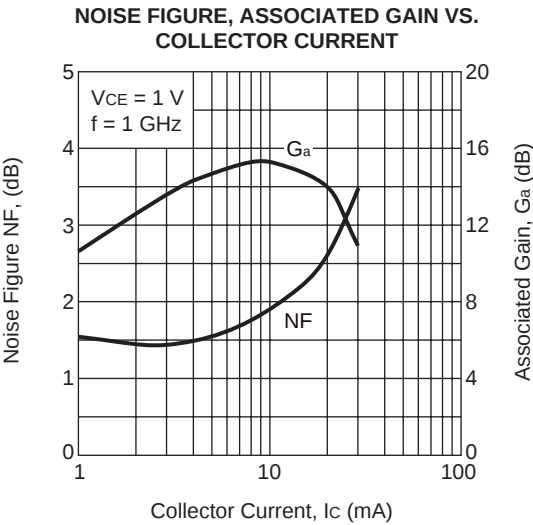
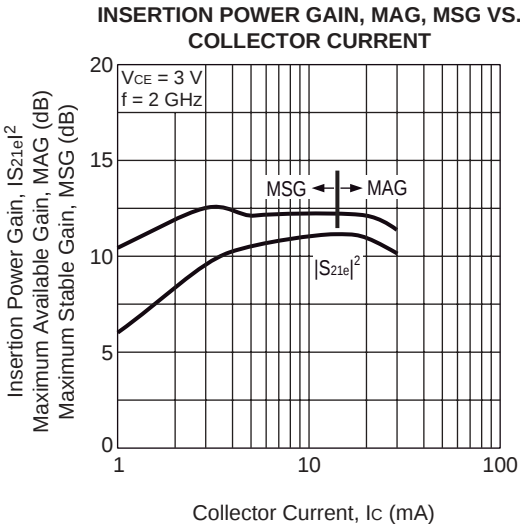
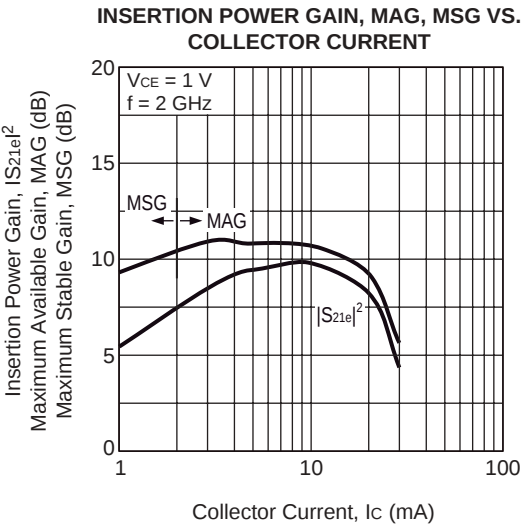
TYPICAL PERFORMANCE CURVES (T_A = 25°C)

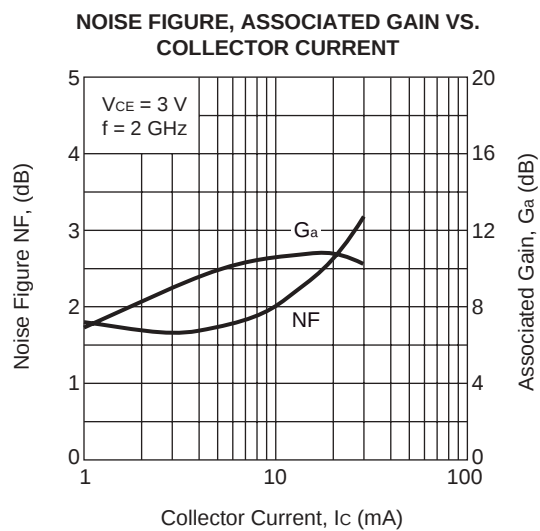
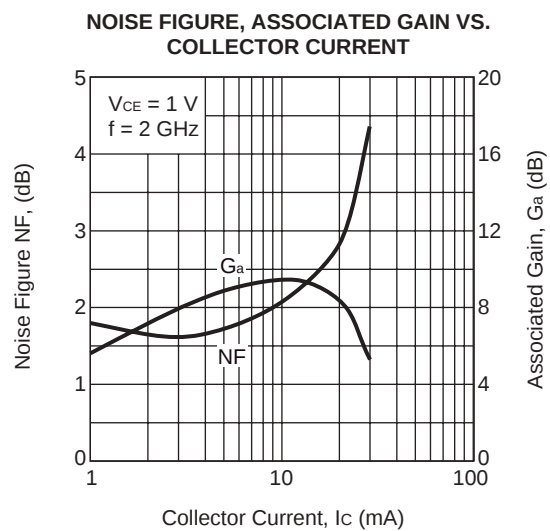


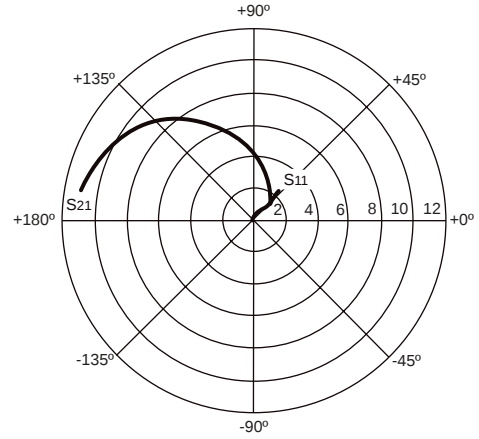
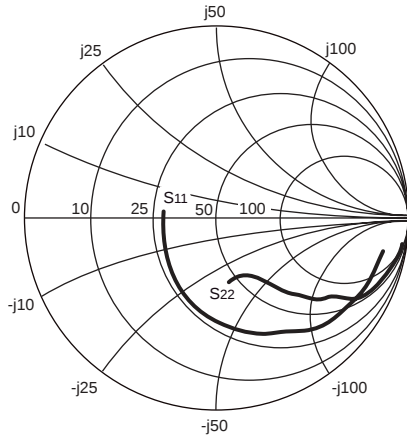
TYPICAL PERFORMANCE CURVES ($T_A = 25^\circ\text{C}$)



TYPICAL PERFORMANCE CURVES (T_A = 25°C)



TYPICAL PERFORMANCE CURVES ($T_A = 25^\circ\text{C}$)

TYPICAL SCATTERING PARAMETERS (T_A = 25°C)

NE685M13

V_c = 2 V, I_c = 5 mA

FREQUENCY	S ₁₁		S ₂₁		S ₁₂		S ₂₂		K	MAG ¹
GHz	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG		(dB)
0.100	0.879	-11.18	10.895	169.79	0.017	85.46	0.980	-8.26	0.05	27.96
0.200	0.854	-24.79	10.531	159.27	0.033	76.47	0.943	-15.79	0.13	25.05
0.300	0.813	-36.17	9.980	150.16	0.047	70.32	0.894	-22.51	0.19	23.25
0.400	0.764	-46.95	9.356	142.00	0.059	65.55	0.843	-28.26	0.24	21.98
0.500	0.677	-58.07	8.645	133.16	0.069	59.99	0.756	-32.30	0.37	21.00
0.600	0.634	-67.22	7.952	127.18	0.077	57.31	0.701	-35.05	0.43	20.16
0.700	0.597	-75.01	7.355	122.04	0.083	55.43	0.657	-38.07	0.47	19.46
0.800	0.560	-82.74	6.818	117.17	0.089	53.53	0.615	-40.74	0.51	18.82
0.900	0.530	-89.38	6.315	113.03	0.095	52.58	0.579	-42.38	0.56	18.24
1.000	0.501	-95.62	5.872	109.14	0.099	51.55	0.542	-44.09	0.61	17.73
1.100	0.478	-101.10	5.483	105.72	0.104	50.81	0.515	-45.60	0.65	17.22
1.200	0.459	-106.13	5.137	102.65	0.108	50.49	0.491	-47.11	0.68	16.79
1.400	0.425	-114.91	4.543	97.14	0.116	50.07	0.451	-49.16	0.76	15.94
1.600	0.399	-122.59	4.068	92.39	0.123	50.09	0.417	-50.64	0.82	15.18
1.800	0.379	-129.37	3.678	88.20	0.131	50.25	0.394	-52.06	0.88	14.49
2.000	0.364	-135.19	3.369	84.36	0.138	50.70	0.377	-53.48	0.92	13.87
2.200	0.350	-140.57	3.103	80.91	0.146	51.06	0.362	-55.00	0.96	13.27
2.400	0.339	-145.78	2.882	77.59	0.154	51.17	0.351	-56.70	0.99	12.73
2.600	0.330	-150.79	2.695	74.45	0.162	51.40	0.343	-58.44	1.02	11.43
2.800	0.321	-155.59	2.529	71.46	0.170	51.61	0.335	-60.35	1.04	10.49
3.000	0.312	-160.44	2.386	68.56	0.178	51.67	0.328	-62.49	1.06	9.75
3.200	0.306	-165.34	2.263	65.81	0.186	51.55	0.324	-65.12	1.08	9.16
3.400	0.301	-170.19	2.150	63.12	0.194	51.53	0.323	-67.74	1.09	8.63
3.600	0.296	-175.11	2.048	60.52	0.202	51.43	0.323	-70.53	1.10	8.14
3.800	0.291	-179.68	1.957	58.06	0.210	51.16	0.327	-73.25	1.10	7.72
4.000	0.286	-176.05	1.874	55.66	0.218	51.06	0.332	-75.87	1.11	7.33

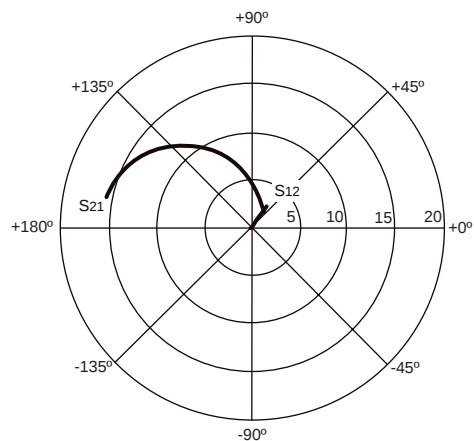
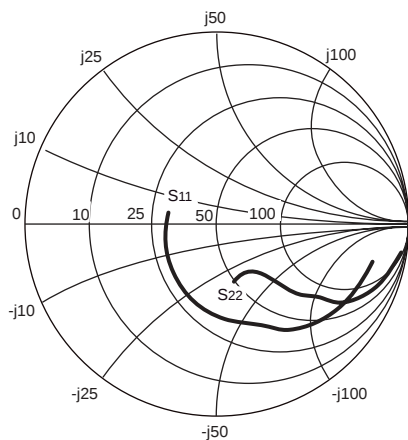
Note:

1. Gain Calculations:

$$\text{MAG} = \frac{|S_{21}|}{|S_{12}|} \left(K \pm \sqrt{K^2 - 1} \right). \text{ When } K \leq 1, \text{ MAG is undefined and MSG values are used. } \text{MSG} = \frac{|S_{21}|}{|S_{12}|}, K = \frac{1 + |\Delta|^2 - |S_{11}|^2 - |S_{22}|^2}{2 |S_{12} S_{21}|}, \Delta = S_{11} S_{22} - S_{21} S_{12}$$

MAG = Maximum Available Gain

MSG = Maximum Stable Gain

TYPICAL SCATTERING PARAMETERS (T_A = 25°C)

NE685M13

V_c = 3 V, I_c = 10 mA

FREQUENCY	S ₁₁		S ₂₁		S ₁₂		S ₂₂		K	MAG ¹
GHz	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG		(dB)
0.100	0.830	-14.89	15.406	167.04	0.015	79.15	0.969	-9.82	0.15	30.06
0.200	0.791	-30.25	14.529	155.17	0.029	74.31	0.918	-18.40	0.18	26.96
0.300	0.734	-43.35	13.385	144.88	0.041	68.95	0.852	-25.66	0.25	25.11
0.400	0.675	-55.24	12.178	136.08	0.050	64.19	0.786	-31.42	0.32	23.86
0.500	0.584	-67.02	10.911	127.43	0.058	59.86	0.690	-34.94	0.46	22.75
0.600	0.541	-76.48	9.839	121.58	0.064	57.87	0.631	-37.08	0.52	21.86
0.700	0.506	-84.40	8.943	116.65	0.069	56.90	0.586	-39.46	0.57	21.10
0.800	0.473	-92.17	8.163	112.19	0.075	55.96	0.546	-41.46	0.62	20.39
0.900	0.448	-98.62	7.477	108.45	0.079	55.53	0.513	-42.47	0.66	19.74
1.000	0.423	-104.84	6.891	104.94	0.083	55.34	0.478	-43.52	0.71	19.17
1.100	0.405	-110.11	6.385	101.90	0.088	55.24	0.455	-44.52	0.75	18.61
1.200	0.390	-114.95	5.947	99.15	0.092	55.23	0.435	-45.57	0.78	18.09
1.400	0.364	-123.47	5.216	94.22	0.100	55.77	0.401	-46.75	0.85	17.16
1.600	0.344	-130.71	4.640	90.04	0.109	56.13	0.373	-47.51	0.90	16.29
1.800	0.329	-137.11	4.179	86.28	0.117	56.73	0.355	-48.39	0.94	15.52
2.000	0.318	-142.56	3.809	82.88	0.126	57.15	0.341	-49.39	0.97	14.81
2.200	0.308	-147.52	3.499	79.73	0.135	57.35	0.330	-50.56	1.00	14.15
2.400	0.300	-152.37	3.242	76.73	0.144	57.60	0.322	-51.97	1.02	12.70
2.600	0.294	-157.24	3.024	73.87	0.153	57.62	0.316	-53.62	1.03	11.86
2.800	0.287	-161.72	2.834	71.13	0.162	57.53	0.310	-55.48	1.05	11.10
3.000	0.282	-166.38	2.670	68.47	0.171	57.39	0.304	-57.60	1.06	10.45
3.200	0.277	-170.99	2.526	65.91	0.180	57.27	0.302	-60.04	1.07	9.89
3.400	0.273	-175.85	2.397	63.40	0.189	56.83	0.301	-62.78	1.07	9.38
3.600	0.270	-179.25	2.282	60.99	0.197	56.62	0.302	-65.63	1.08	8.91
3.800	0.266	-174.83	2.179	58.67	0.207	56.19	0.306	-68.43	1.08	8.51
4.000	0.263	-170.53	2.084	56.42	0.215	55.67	0.311	-71.13	1.08	8.11

Note:

1. Gain Calculations:

$$\text{MAG} = \frac{|S_{21}|}{|S_{12}|} \left(K \pm \sqrt{K^2 - 1} \right). \text{ When } K \leq 1, \text{ MAG is undefined and MSG values are used. } \text{MSG} = \frac{|S_{21}|}{|S_{12}|}, K = \frac{1 + |\Delta|^2 - |S_{11}|^2 - |S_{22}|^2}{2 |S_{12} S_{21}|}, \Delta = S_{11} S_{22} - S_{21} S_{12}$$

MAG = Maximum Available Gain

MSG = Maximum Stable Gain

NE685M13 NONLINEAR MODEL

BJT NONLINEAR MODEL PARAMETERS (1)

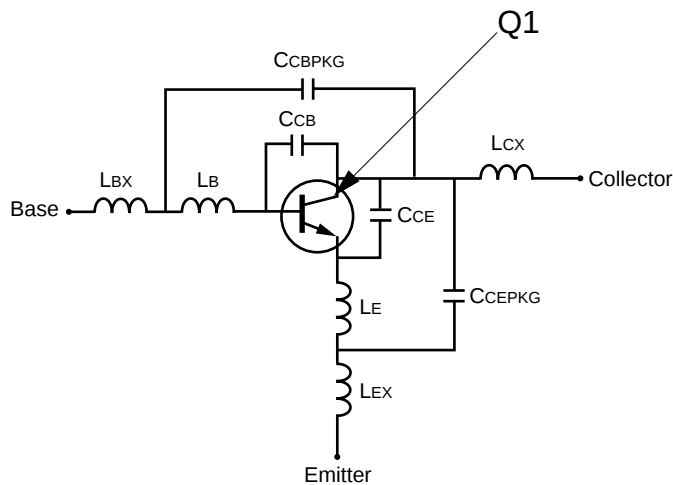
Parameters	Q1	Parameters	Q1
IS	7e-16	MJC	0.34
BF	109	XCJC	0.7
NF	1	CJS	0
VAF	15	VJS	0.75
IKF	0.19	MJS	0
ISE	7.9e-13	FC	0.5
NE	2.19	TF	2.5e-12
BR	1	XTF	5.2
NR	1.08	VTF	4.58
VAR	12.4	ITF	0.011
IKR	0	PTF	0
ISC	0	TR	1e-9
NC	2	EG	1.11
RE	1.3	XTB	0
RB	10	XTI	3
RBM	8.34	KF	0
IRB	0.009	AF	1
RC	10		
CJE	0.4e-12		
VJE	0.812		
MJE	0.5		
CJC	0.18e-12		
VJC	0.75		

(1) Gummel-Poon Model

UNITS

Parameter	Units
time	seconds (S)
capacitance	farads (F)
inductance	henries (H)
resistance	ohms (Ω)
voltage	volts (V)
current	amps (A)

SCHEMATIC



ADDITIONAL PARAMETERS

Parameters	68533
CCB	0.1e-12
CCE	0.14e-12
LB	0.35e-9
LE	0.4e-9
CCBPKG	0.05e-12
CCEPKG	0.05e-12
LBX	0.05e-9
LCX	0.05e-9
LEX	0.05e-9

MODEL RANGE

Frequency: 0.1 to 4.0 GHz
Bias: VCE = 0.5 V to 3 V, IC = 0.5 mA to 20 mA
Date: 09/02

Life Support Applications
These NEC products are not intended for use in life support devices, appliances, or systems where the malfunction of these products can reasonably be expected to result in personal injury. The customers of CEL using or selling these products for use in such applications do so at their own risk and agree to fully indemnify CEL for all damages resulting from such improper use or sale.

CEL California Eastern Laboratories, Your source for NEC RF, Microwave, Optoelectronic, and Fiber Optic Semiconductor Devices.
4590 Patrick Henry Drive • Santa Clara, CA 95054-1817 • (408) 988-3500 • FAX (408) 988-0279 • www.cel.com

DATA SUBJECT TO CHANGE WITHOUT NOTICE

09/17/2002